

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-6.0	V
Collector Current	I _C	-200	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Base Current	I _{BM}	-100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

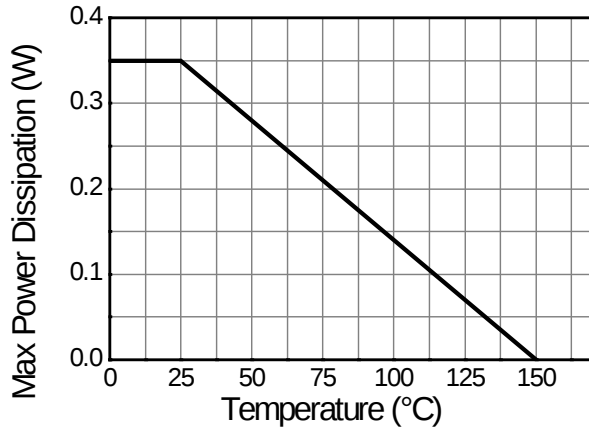
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	310	mW
		350	
Thermal Resistance, Junction to Ambient	R _{θJA}	403	°C/W
		357	
Thermal Resistance, Junction to Leads	R _{θJL}	350	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

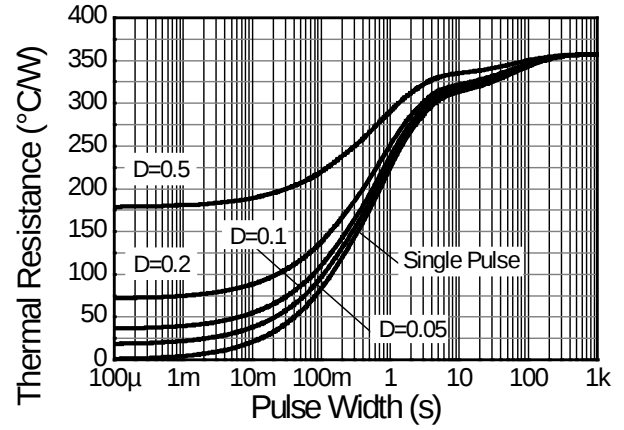
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; the device is measured under still air conditions while operating in a steady-state.
 7. Same as Note 6 except the device is mounted on 15 mm × 15mm 1oz copper.
 8. Thermal resistance from junction to solder-point (at the end of the leads).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

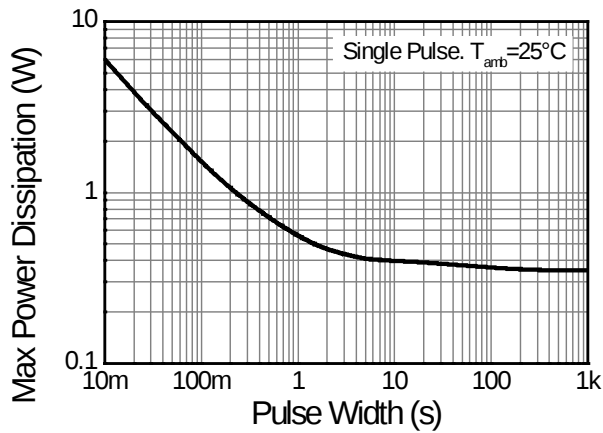
Thermal Characteristics and Derating Information



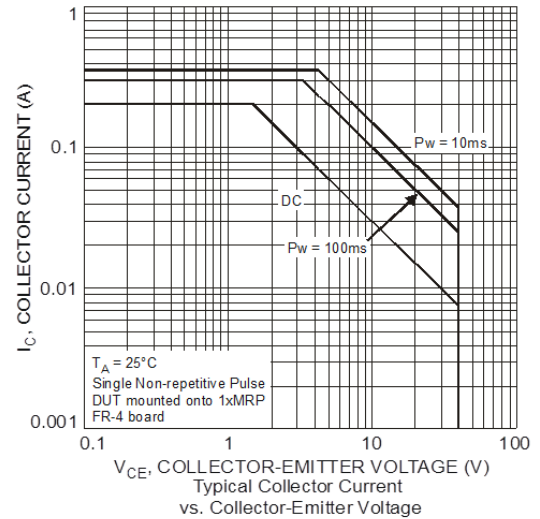
Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



Typical Collector Current vs. Collector-Emitter Voltage

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	-40	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-40	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-6.0	—	V	I _E = -100μA, I _C = 0
Collector Cutoff Current	I _{CEV}	—	-50	nA	V _{CE} = -30V, V _{BE} = 3.0V
		—	-50	nA	V _{CE} = -30V, V _{BE} = -0.25V
Emitter-Base Cutoff Current	I _{EBO}	—	-50	nA	V _{EB} = -5V
ON CHARACTERISTICS (Note 10)					
DC Current Gain	h _{FE}	60	—	—	I _C = -100μA, V _{CE} = -1.0V
		80	—		I _C = -1.0mA, V _{CE} = -1.0V
		100	300		I _C = -10mA, V _{CE} = -1.0V
		60	—		I _C = -50mA, V _{CE} = -1.0V
		30	—		I _C = -100mA, V _{CE} = -1.0V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	-0.25 -0.40	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	-0.65 —	-0.85 -0.95	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.5	pF	V _{CB} = -5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	10	pF	V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	2.0	12	kΩ	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.1	10	× 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	100	400	—	
Output Admittance	h _{oe}	3.0	60	μS	V _{CE} = -20V, I _C = -10mA, f = 100MHz
Current Gain-Bandwidth Product	f _T	250	—	MHz	
Noise Figure	NF	—	4.0	dB	V _{CE} = -5.0V, I _C = -100μA, R _S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = -3.0V, I _C = -10mA,
Rise Time	t _r	—	35	ns	V _{BE(off)} = 0.5V, I _{B1} = -1.0mA
Storage Time	t _s	—	225	ns	V _{CC} = -3.0V, I _C = -10mA,
Fall Time	t _f	—	75	ns	I _{B1} = I _{B2} = -1.0mA

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

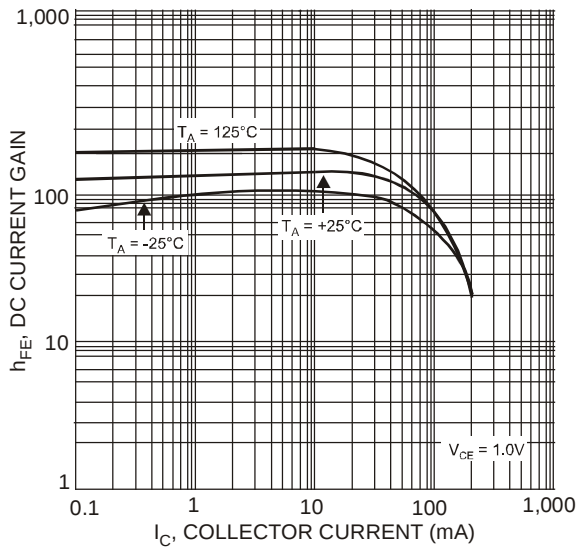


Figure 1 Typical DC Current Gain vs. Collector Current

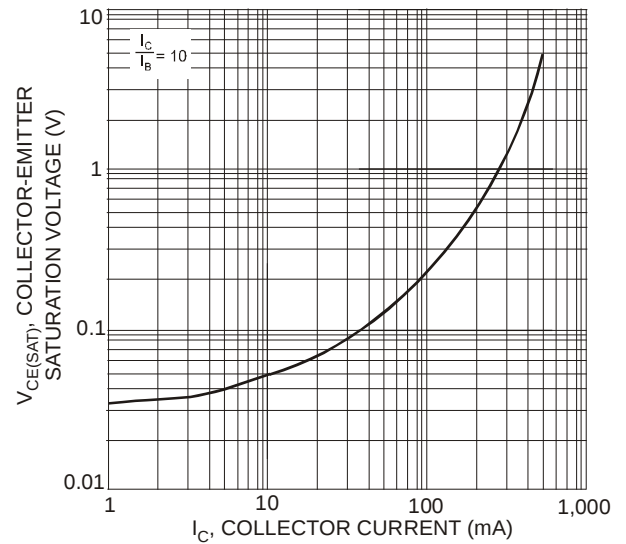


Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

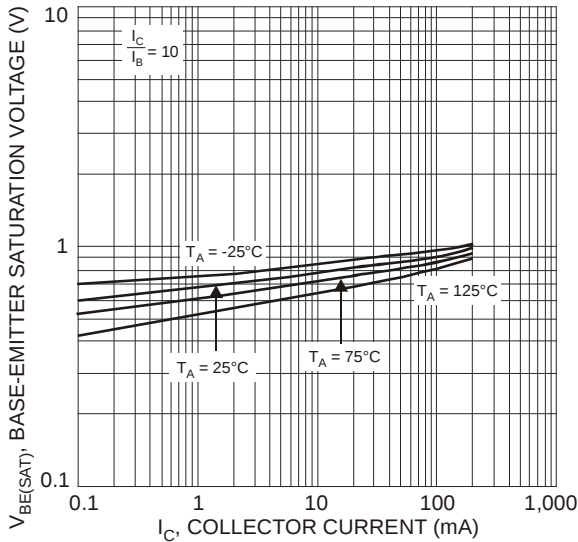


Figure 3 Typical Base-Emitter Saturation Voltage vs. Collector Current

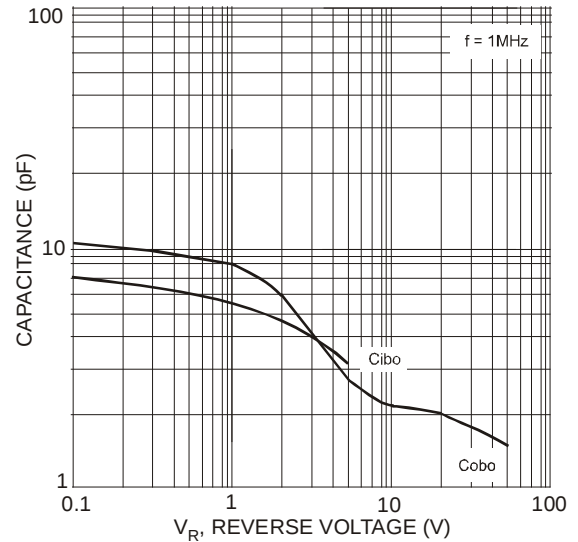
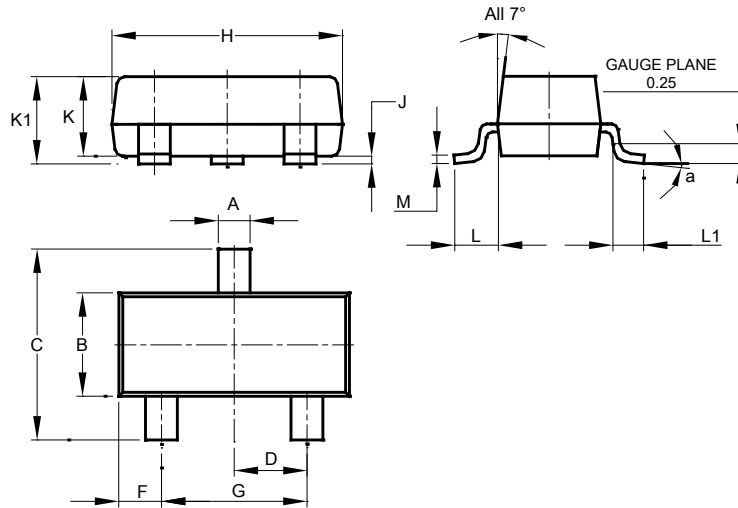


Figure 4 Typical Capacitance Characteristics

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

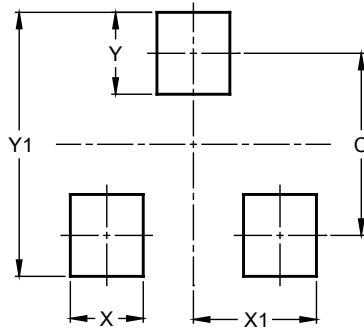


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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